

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	69	(semiconduct\$4) near3 (film sheet layer pad) near3 (metal\$4 conductive) near3 (shunt\$4 "contacts") near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:13
L2	62	1 and (substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:16
L3	21	2 and (strain stress load\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:14
L4	15	3 and (resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:17
L5	3851	(metal\$4 conductive) near3 (shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:15
L6	329	5 and (semiconduct\$4) near3 (film sheet layer pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:21
L7	121	6 and (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:22
L8	117	7 and (substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:22
L9	5	8 and (strain stress load\$4) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:14

L10	20313	(strain stress load\$4) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:15
L11	5	9 and (strain stress load\$4 pressure force) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:23
L12	8	10 and (metal\$4 conductive) near3 (shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:21
L13	1517	10 and (metal\$4 conductive) near3 (shunt\$4 contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:16
L14	453	13 and (semiconduct\$4) near3 (film sheet layer pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:16
L15	437	14 and (substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:17
L16	289	15 and (resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:17
L17	191	16 and (voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:18
L18	27	16 and (measur\$4 sens\$4 detect\$4 transducer) near3 (voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:18
L19	64964	(semiconduct\$4) near3 (film sheet layer pad).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:21

L20	3084	19 and (metal\$4) near3 (shunt\$4 contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:22
L21	2357	20 and (substrate).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:22
L22	170	21 and (interface).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:22
L23	6	22 and (strain stress load\$4 pressure force) near3 (interface).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:24
L24	0	(strain stress load\$4 pressure force) near3 (interface) near3 (chang\$4) near3 (resistance) near3 (semiconduct\$4) near3 (film pad sheet layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:25

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L1	2390	(semiconduct\$4) near3 (film layer sheet pad) near3 (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L2	22	1 and (stress strain load\$4 force pressure) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L3	24	(interface) near3 (between) near3 (semiconduct\$4) near3 (film layer sheet pad) near3 (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L4	17	"4725877"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L5	11	4 and (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L6	1	5 and (stress strain load\$4 force pressure) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L7	1	6 and (semiconduct\$4) near3 (film layer sheet pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L8	0	7 and (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:42
L9	1	7 and (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:42

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L1	2390	(semiconduct\$4) near3 (film layer sheet pad) near3 (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L2	22	1 and (stress strain load\$4 force pressure) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L3	24	(interface) near3 (between) near3 (semiconduct\$4) near3 (film layer sheet pad) near3 (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L4	17	"4725877"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L5	11	4 and (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L6	1	5 and (stress strain load\$4 force pressure) near3 (interface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L7	1	6 and (semiconduct\$4) near3 (film layer sheet pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:41
L8	0	7 and (metal\$4) near3 (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:42
L9	1	7 and (contact shunt\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/13 12:42